

**SUPPLEMENTAL AMENDMENT  
U.S. Appln. No. 09/900,962****Attorney Docket Q61744****REMARKS**

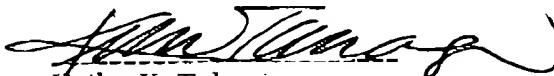
Claims 8-14 are all the claims pending in this application. Claim 8 has been amended to recite that the catalyst layer comprises a metal, alloy or metallic compound containing at least one element selected from the group consisting of Ni, Co, Fe, Mn, Cr, V, Ti, Re, W, Ta, Hf, Lu, Gd, Ce, La, Ru, Mo, Zr, Y, Au, Ag, Cu, Al and Bi, and have amended claim 10 to delete the recitation directed to the materials comprised in the catalyst layer.

The Examiner indicated that the above amendments to the claims would place the application in condition for allowance. Accordingly, entry of the above amendment is respectfully requested.

In view of the above, allowance of this application are now believed to be in order, and such actions are hereby solicited. If any points remain in issue which the Examiner feels may be best resolved through a personal or telephone interview, the Examiner is kindly requested to contact the undersigned at the telephone number listed below.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,



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**SUPPLEMENTAL AMENDMENT  
U.S. Appln. No. 09/900,962****Attorney Docket Q61744****APPENDIX****VERSION WITH MARKINGS TO SHOW CHANGES MADE****IN THE CLAIMS:**

The claims have been changed as follows.

8. (twice amended) A method for producing a gallium nitride-based compound semiconductor light-emitting device comprising providing an n-type layer and a light-emitting layer each comprising a gallium nitride-based compound semiconductor, providing a p-type layer comprising a gallium nitride-based compound semiconductor through the following steps:

producing a gallium nitride-based compound semiconductor layer doped with a p-type impurity;

producing a catalyst layer comprising a metal, alloy or metallic compound containing at least one element selected from the group consisting of Ni, Co, Fe, Mn, Cr, V, Ti, Re, W, Ta, Hf, Lu, Gd, Ce, La, Ru, Mo, Zr, Y, Au, Ag, Cu, Al and Bi on said gallium nitride-compound semiconductor layer;

annealing the gallium nitride-based compound semiconductor layer fixed with said catalyst layer in an atmosphere gas containing no oxygen;

stripping said catalyst layer completely; and

providing a p-side electrode on said p-type layer after annealing.

10. (amended) The method for producing a gallium nitride-based compound semiconductor light-emitting device as claimed in claim 9, wherein said catalyst layer is a monolayer or multilayer film ~~comprising a metal, alloy or compound containing at least one element selected from the group consisting of Ni, Co, Fe, Mn, Cr, V, Ti, Re, W, Ta, Hf, Lu, Gd, Ce, La, Ru, Mo, Zr, Y, Au, Ag, Cu, Al and Bi.~~